

Abstract

Method for depositing an epitaxial layer on a substrate wafer

- 5 A method for depositing an epitaxial layer on a substrate wafer from a vapor phase, comprising
- measuring an edge geometry of the substrate wafer that assigns a thickness characteristic value to an edge of the substrate wafer as a function of edge positions;
- placing the substrate wafer in a pocket of a susceptor of a device for depositing the
- 10 epitaxial layer, the pocket being surrounded by a boundary with a circular circumference;
- heating the substrate wafer; and
- passing process gas over the substrate wafer;
- which comprises
- 15 placing the substrate wafer in the pocket such that the distance from the substrate wafer to the boundary of the pocket is smaller at edge positions with the thickness characteristic value of a thicker edge than at edge positions with the thickness characteristic value of a thinner edge.

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Drawing for the abstract: Fig. 2